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## LIST OF REFERENCES CITED BY APPLICANT

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Kentarō NAKAJIMA, et al.

FILING DATE

September 12, 2003

GROUP

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DM	AA	5,940,319	08/17/1999	M. DURLAM, et al.			
DM	AB	5,956,267	09/21/1999	A. T. HURST, et al.			
DM	AC	5,946,228	08/31/1999	D. W. ABRAHAM, et al.			
DM	AD	6,072,718	06/06/2000	D. W. ABRAHAM, et al.			
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DM	AF	6,005,800	12/21/1999	R. H. KOCH, et al.			
DM	AG	6,081,445	06/27/2000	J. SHI, et al.			
DM	AH	6,134,139	10/17/2000	M. K. BHATTACHARYYA, et al.			
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	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
DM	AO	WO 001/10172	02/24/2000	WIPO (with English Abstract and corr. JP 2002-522915)		X
DM	AP	2002-522915	07/23/2002	JAPAN		X
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## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

DM	AV	S. TEHRANI, et al., Journal of Applied Physics, Magnetoresistive Magnetic Random Access Memory, vol. 85, no. 8, pages 5822-5827, "HIGH DENSITY SUBMICRON MAGNETORESISTIVE RANDOM ACCESS MEMORY (INVITED)", April 15, 1999	
DM	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, ISSCC 2000 / Session 7 / TD: Emerging Memory & Device Technologies / Paper TA 7.2, pages 128-129, "A 10ns READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", February 8, 2000	
DM	AX	M. SATO, et al., IEEE Transactions on Magnetics, vol. 33, no. 5, pages 3553-3555, "SPIN-VALVE-LIKE PROPERTIES AND ANNEALING EFFECT IN FERROMAGNETIC TUNNEL JUNCTIONS", September 1997	
DM	AY	M. SATO, et al., Jpn. J. Appl. Phys. vol. 36, part 2, no. 2B, pages L 200-L 201, "SPIN-VALVE-LIKE PROPERTIES OF FERROMAGNETIC TUNNEL JUNCTIONS", February 15, 1997	
DM	AZ	K. INOMATA, et al., Jpn. J. Appl. Phys. vol. 36, part 2, no. 10B, pages L 1380-L 1383, "SPIN-DEPENDENT TUNNELING BETWEEN A SOFT FERROMAGNETIC LAYER AND HARD MAGNETIC NANOSIZE PARTICLES", October 15, 1997	<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

6/8/05

\*Examiner: Initial if reference is considered. Whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.